

2825

Attorney Docket No.: <u>NICHIA-00800</u>

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In	re	Application	of:
111	10	Application	01:

Shinichi Nagahama et al.

Serial No.: 09/500,288 \

Filed: February 8, 2000

For: NITRIDE SEMICONDUCTOR)
DEVICE AND MANUFACTURING)

METHOD THEREOF

Group:

Art Unit: 2825

Examiner:

TRANSMITTAL LETTER

260 Sheridan Avenue, Suite 420

Palo Alto, CA 94306 (650) 833-0160

venue, Suite 420

Assistant Commissioner for Patents Washington, D.C. 20231

Sir:

Enclosed please find an Information Disclosure Statement and Form PTO-1449, including copies of the references contained thereon, for filing in the U.S. Patent and Trademark Office.

The Commissioner is hereby authorized to charge any additional fee or credit overpayment to our Deposit Account No. <u>08-1275</u>. An originally executed duplicate of this transmittal is enclosed for this purpose.

Respectfully submitted,

HAVERSTOCK & OWENS LLP

Dated: 9-8-00

Thomas B. Haverstock

Reg. No.: 32,571

Attorneys for Applicants

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In re A	Application of:	Group Art Unit: 2825	
Shinic	hi Nagahama <i>et al</i> .	Examiner:	
Serial	No.: 09/500,288	INFORMATION DISCLOSURE STATEMENT	
Filed:	February 8, 2000	260 Sheridan Avenue, Suite 420	
For:	NITRIDE SEMICONDUCTOR) DEVICE AND MANUFACTURING) METHOD THEREOF	Palo Alto, California 94306	•

Assistant Commissioner for Patents Washington, D.C. 20231

Sir:

The citations listed below, copies attached, may be material to the examination of the above-identified application, and are therefore submitted in compliance with the duty of disclosure defined in 37 C.F.R. §§ 1.56 and 1.97. The Examiner is requested to make these citations of official record in this application.

Applicants have become aware of the following printed publications which may be material to the examination of this application:

- Japanese Publication No.: 04144294;
- Japanese Publication No.: 09180998;
- Japanese Publication No.: 09246651;
- Japanese Publication No.: 09260772;
- Japanese Publication No.: 09293935;
- Japanese Publication No.: 10242565;
- Japanese Publication No.: 10256645;
- Japanese Publication No.: 10270792;

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- Japanese Publication No.: 10290027;
- Japanese Publication No.: 10294529;
- Japanese Publication No.: 10321962;
- Japanese Publication No.: 11040893;
- Japanese Publication No.: 2000-31599;
- German Publication No.: DE 196 48 955A1; and
- "InGaN/GaN/AIGaN-based laser diodes with modulation-doped strained-layer superlattices grown on an epitaxially laterally overgrown GaN substrate," Shuji Nakamura et al., Applied Physics Letter, Vol. 72, No. 2, January 12, 1998..

This Information Disclosure Statement under 37 C.F.R. §§ 1.56 and 1.97 is not to be construed as a representation that a search has been made, that additional information material to the examination of this application does not exist, or that anyone or more of these citations constitutes prior art.

Respectfully submitted,

HAVERSTOCK & OWENS LLP

Dated: 9-8-00

Thomas B. Haverstock Reg. No.: 32,571

Attorneys for Applicants

CERTIFICATE OF MAILING (37 CFR \$ 1.8(a))

I hereby nertify that this paper railong with any referred to achieve attached in enclosed) is being deposited with that J.B. Postal Service on the date shown becomes to sufficient postage as first class mail in an enumber addressed to the Assistant Commissione for matchieves washington D.C. 20231

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